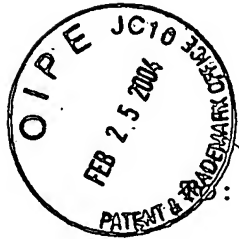


TSMC-01-1488



February 19, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/666,359 09/19/03 |

Chi-Chun Chen et al.

METHOD OF FORMING AN ULTRATHIN  
NITRIDE/OXIDE STACK AS A GATE  
DIELECTRIC

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on February 23, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 2/23/04

TSMC-01-1488

Taiwan Patent NP-0763-TW discusses the step coverage capability of TEOS-SiO<sub>2</sub> being excellent and a SiO<sub>2</sub>LPCVD reaction mainly using TEOS being widely adopted in the semiconductor industry.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a large, stylized loop at the end.

Stephen B. Ackerman,  
Reg. No. 37761

(Use several shouts if necessary)

10/666,359

Chi-Chun Chen et al.

09/19/03

Group Art Unit

EXAMINER  
INITIAL

DOCUMENT NUMBER

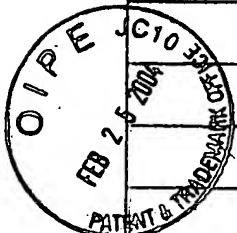
DATE

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## DOCUMENT NUMBER

DATE \_\_\_\_\_

COUNTRY

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### Translation

YES

NO

NP-0763-TW 6/17/03 Taiwan

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

EXPLANATION

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.